2SC2712GT1G

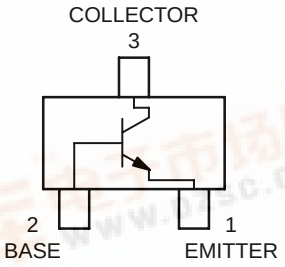
Medium Frequency NPN Amplifier Transistor

50 V, 200 mA, 80 MHz

ON Semiconductor®

http://onsemi.com

The 2SC2712GT1G is designed for low to medium frequency applications such as wireless toys. The targeted design enables improved performance versus the industry standard MMBT3904* in some key parametric specifications.



SC−59
CASE 318D
STYLE 1

Features

- Lower $V_{CE(sat)}$*
- Higher Gain (h_{fe})*
- Higher Breakdown Voltage Rating*
- Moisture Sensitivity Level: 1
- This is a Pb−Free Device

Benefits

- Longer Battery Life
- Improved Performance Through Targeted Design

MAXIMUM RATINGS (T_A = 25°C)

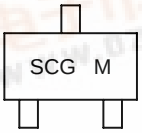
Rating	Symbol	Value	Unit
Collector−Base Voltage	$V_{(BR)CBO}$	60	Vdc
Collector−Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter−Base Voltage	$V_{(BR)EBO}$	5.0	Vdc
Collector Current − Continuous	I_C	150	mAdc
Collector Current − Peak	$I_{C(P)}$	200	mAdc
Base Current	I_B	30	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.
*Specifications compared to MMBT3904.

MARKING DIAGRAMS



SCG = Specific Date Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
2SC2712GT1G	SC−59 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Collector−Emitter Breakdown Voltage (I_C = 2.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	−	Vdc
Collector−Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	60	−	Vdc
Emitter−Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	−	Vdc
Collector−Base Cutoff Current (V_{CB} = 60 Vdc, I_E = 0)	I_{CBO}	−	0.1	μAdc
Emitter Cut−off Current (V_{EB} = 5 V, I_C = 0 V)	I_{EBO}	−	0.1	μA
Collector−Emitter Cutoff Current (V_{CE} = 10 Vdc, I_B = 0) (V_{CE} = 30 Vdc, I_B = 0) (V_{CE} = 30 Vdc, I_B = 0, T_A = 80°C)	I_{CEO}	 − − −	 0.1 2.0 1.0	 μAdc μAdc mAdc
DC Current Gain (Note 1) (V_{CE} = 6.0 Vdc, I_C = 2.0 mAdc)	h_{FE}	200	400	−
Collector−Emitter Saturation Voltage (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$	−	0.25	Vdc

SMALL−SIGNAL CHARACTERISTICS

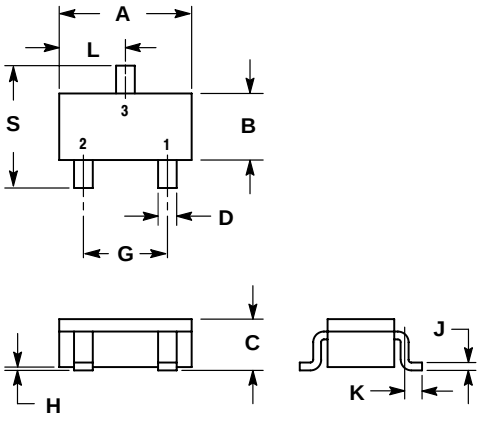
Current−Gain − Bandwidth Product (I_C = 1.0 mA, V_{CE} = 10.0 V, f = 10 MHz)	f_T	80	−	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)	C_{obo}	−	3.5	pF
Noise Figure (I_C = 0.1 mA, V_{CE} = 6.0 Vdc, R_S = 10 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	−	10	dB

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

2SC2712GT1G

PACKAGE DIMENSIONS

SC−59
CASE 318D−04
ISSUE F

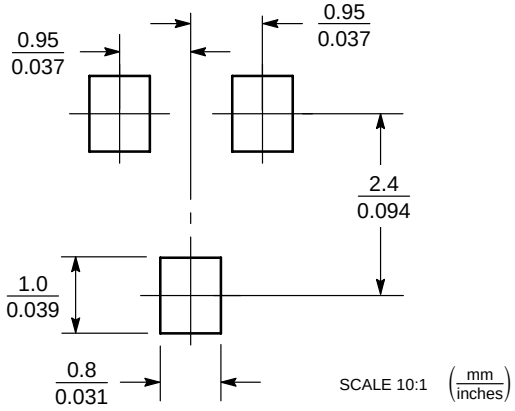


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.70	3.10	0.1063	0.1220
B	1.30	1.70	0.0512	0.0669
C	1.00	1.30	0.0394	0.0511
D	0.35	0.50	0.0138	0.0196
G	1.70	2.10	0.0670	0.0826
H	0.013	0.100	0.0005	0.0040
J	0.09	0.18	0.0034	0.0070
K	0.20	0.60	0.0079	0.0236
L	1.25	1.65	0.0493	0.0649
S	2.50	3.00	0.0985	0.1181

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2SC2712GT1G

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

2SC2712GT1/D